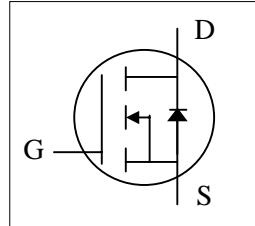
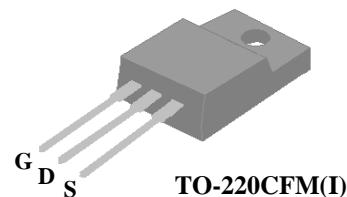




- ▼ Low On-resistance
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free



BV_{DSS}	500V
$R_{DS(ON)}$	0.52Ω
I_D	14A



Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220CFM isolation package is widely preferred for commercial-industrial through hole applications.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	500	V
V_{GS}	Gate-Source Voltage	+30	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	14	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	9	A
I_{DM}	Pulsed Drain Current ¹	50	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	39	W
	Linear Derating Factor	0.31	W/ $^\circ C$
E_{AS}	Single Pulse Avalanche Energy ²	98	mJ
I_{AR}	Avalanche Current	14	A
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Units
R_{thj-c}	Maximum Thermal Resistance, Junction-case	3.2	$^\circ C/W$
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient	65	$^\circ C/W$



Electrical Characteristics@ $T_j=25^\circ C$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=1mA$	500	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ³	$V_{GS}=10V, I_D=7A$	-	-	0.52	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2	-	4	V
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=7A$	-	11	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=400V, V_{GS}=0V$	-	-	100	μA
I_{GSS}	Gate-Source Leakage	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	± 100	nA
Q_g	Total Gate Charge ³	$I_D=14A$	-	42	77	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=200V$	-	13	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{GS}=10V$	-	14	-	nC
$t_{d(on)}$	Turn-on Delay Time ³	$V_{DD}=200V$	-	45	-	ns
t_r	Rise Time	$I_D=7A$	-	50	-	ns
$t_{d(off)}$	Turn-off Delay Time	$R_G=50\Omega$	-	230	-	ns
t_f	Fall Time	$V_{GS}=10V$	-	55	-	ns
C_{iss}	Input Capacitance	$V_{GS}=0V$	-	2300	3170	pF
C_{oss}	Output Capacitance	$V_{DS}=30V$	-	180	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	6	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ³	$I_S=14A, V_{GS}=0V$	-	-	1.3	V
t_{rr}	Reverse Recovery Time ³	$I_S=14A, V_{GS}=0V$	-	430	-	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100A/\mu s$	-	7.6	-	μC

Notes:

- 1.Pulse width limited by Max junction temperature.
- 2.Starting $T_j=25^\circ C$, $V_{DD}=50V$, $L=1mH$, $R_G=25\Omega$
- 3.Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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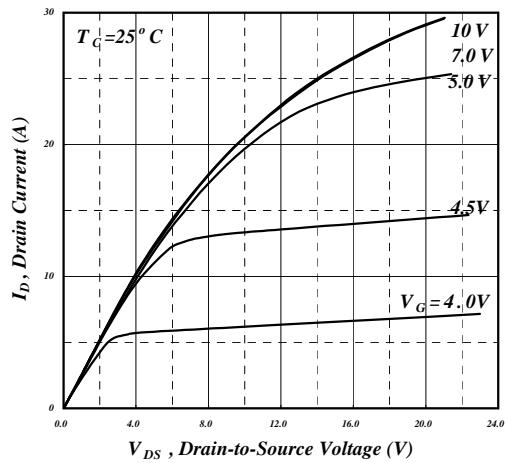


Fig 1. Typical Output Characteristics

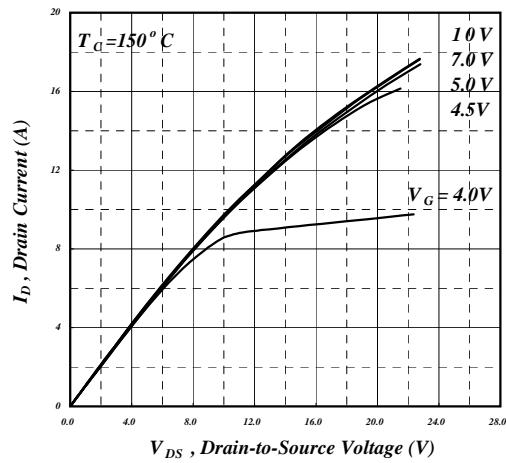


Fig 2. Typical Output Characteristics

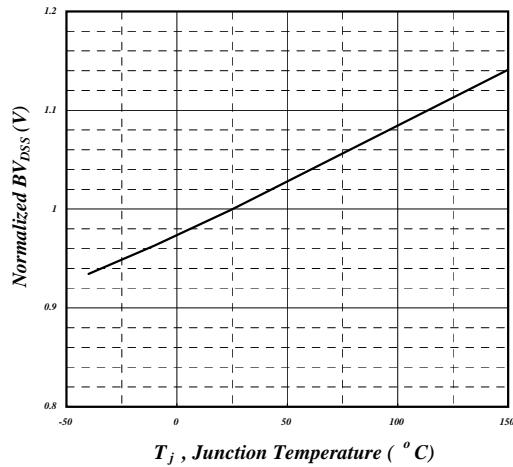
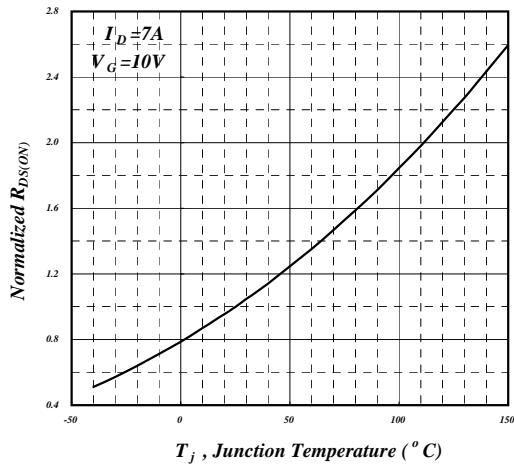
Fig 3. Normalized BV_{DSS} v.s. Junction Temperature

Fig 4. Normalized On-Resistance v.s. Junction Temperature

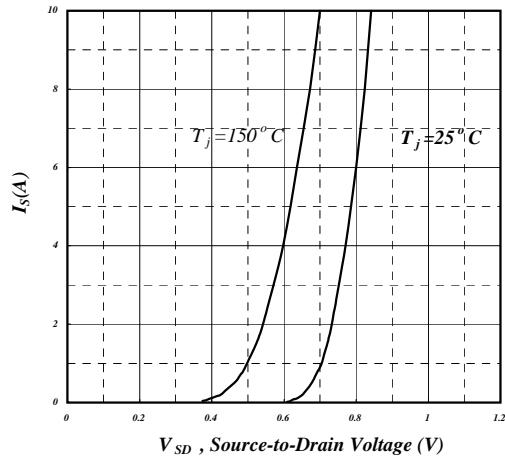


Fig 5. Forward Characteristic of Reverse Diode

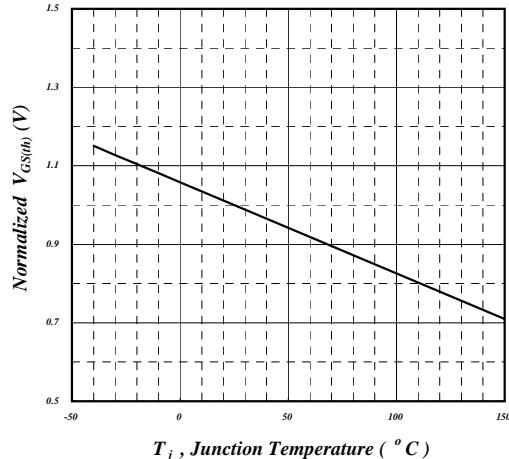


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



AP13N50I-HF

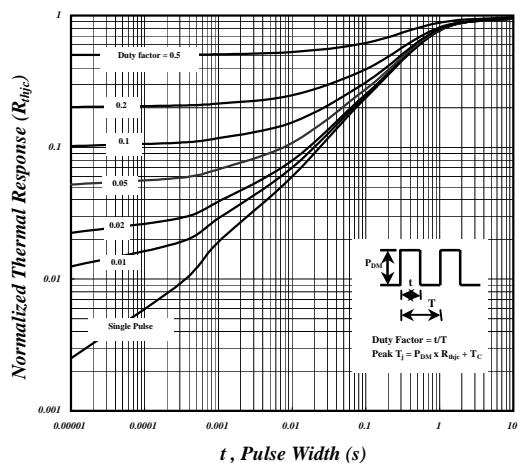
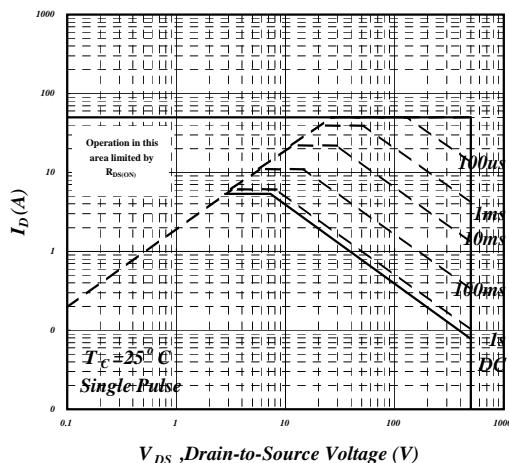
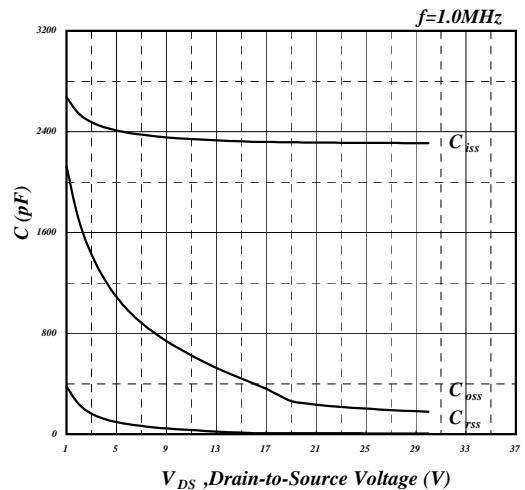
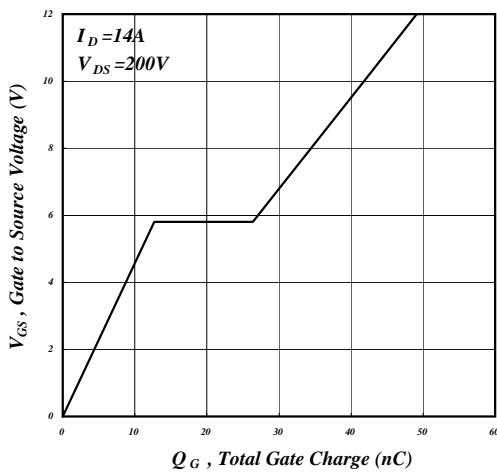


Fig 11. Switching Time Waveform

